PTO/SB/08A (08-03)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	10/625,811
Filing Date	7/23/2003
First Named Inventor	Christopher L. Chua
Art Unit	2828
Examiner Name	Tuan N. Nguyen
Attorney Docket Number	A3316-US-NP

U.S. Patent Documents

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TN		US-6,208,681	03/27/2001	Thornton	
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Non Patent Literature Documents

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T[3]
TN		D.L HUFFAKER, ET AL.: Appl, Phys. Lett, Vol 65, no 1 pp 97-99, 1994	☐
TN		G.R. HADLEY: Optic Letters, Vol 20, no 13, pp 1483-1485, 1995	☐
TN		S. MUKAI, ETAL: Appl Phys. Lett, Vol 45, no8, pp834-835, 1984	☐
			☐

Examiner Signature	Tuan Nguyen	Date Considered	8/23/06

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[1] Applicant's unique citation description number (optional). [2] Applicant is to place a check mark here if English Translation is attached.

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Form PTO-1449 (REV. 1/06) US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. A3316-US-NP	APPLICATION NO. 10/625,811
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	APPLICANT(S) Christopher L. Chua	
	FILING DATE 7/23/2003	GROUP 2828

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